

FDD6030BL/FDU6030BL

30V N-Channel PowerTrench[®] MOSFET

General Description

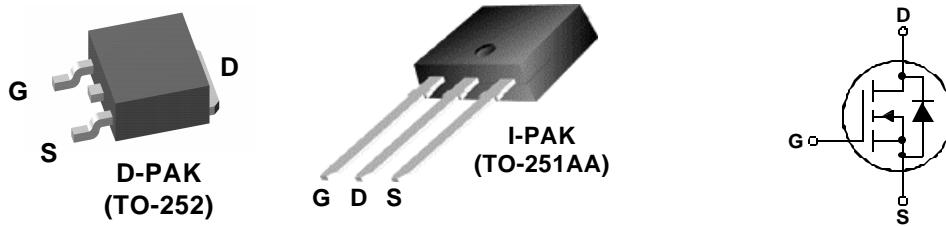
This N-Channel MOSFET has been designed specifically to improve the overall efficiency of DC/DC converters using either synchronous or conventional switching PWM controllers. It has been optimized for low gate charge, low $R_{DS(ON)}$, fast switching speed and extremely low $R_{DS(ON)}$ in a small package.

Applications

- DC/DC converter
- Motor drives

Features

- 42 A, 30 V $R_{DS(ON)} = 16 \text{ m}\Omega$ @ $V_{GS} = 10 \text{ V}$
 $R_{DS(ON)} = 22 \text{ m}\Omega$ @ $V_{GS} = 4.5 \text{ V}$
- Low gate charge (22 nC typical)
- Fast switching
- High performance trench technology for extremely low $R_{DS(ON)}$



Absolute Maximum Ratings

$T_A=25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Ratings	Units
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	V
I_D	Continuous Drain Current @ $T_C=25^\circ\text{C}$ (Note 3)	42	A
	@ $T_A=25^\circ\text{C}$ (Note 1a)	10	
	Pulsed (Note 1a)	100	
P_D	Power Dissipation @ $T_C=25^\circ\text{C}$ (Note 3)	50	W
	@ $T_A=25^\circ\text{C}$ (Note 1a)	3.8	
	@ $T_A=25^\circ\text{C}$ (Note 1b)	1.6	
T_J, T_{STG}	Operating and Storage Junction Temperature Range	-55 to +175	°C

Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction-to-Case (Note 1)	3.0	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1a)	45	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient (Note 1b)	96	°C/W

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape width	Quantity
FDD6030BL	FDD6030BL	D-PAK (TO-252)	13"	12mm	2500 units
FDU6030BL	FDU6030BL	I-PAK (TO-251)	Tube	N/A	75

Electrical Characteristics						
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Avalanche Ratings (Note 2)						
W _{DSS}	Drain-Source Avalanche Energy	Single Pulse, V _{DD} = 15 V			130	mJ
I _{AR}	Drain-Source Avalanche Current				10	A
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0 V, I _D = 250 μ A	30			V
Δ BV _{DSS} Δ T _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μ A, Referenced to 25°C		22		mV/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 24 V, V _{GS} = 0 V			1	μ A
I _{GSSF}	Gate-Body Leakage, Forward	V _{GS} = 20 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage, Reverse	V _{GS} = -20 V, V _{DS} = 0 V			-100	nA
On Characteristics (Note 2)						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 250 μ A	1	1.6	3	V
Δ V _{GS(th)} Δ T _J	Gate Threshold Voltage Temperature Coefficient	I _D = 250 μ A, Referenced to 25°C		-4		mV/°C
R _{D(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 10 A V _{GS} = 4.5 V, I _D = 8.4 A V _{GS} = 10 V, I _D = 10 A, T _J =125°C		12 17 19	16 22 26	m Ω
I _{D(on)}	On-State Drain Current	V _{GS} = 10 V, V _{DS} = 5 V	50			A
g _F	Forward Transconductance	V _{DS} = 10 V, I _D = 10 A		29		S
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = 15 V, V _{GS} = 0 V, f = 1.0 MHz		1143		pF
C _{oss}	Output Capacitance			249		pF
C _{rss}	Reverse Transfer Capacitance			107		pF
Switching Characteristics (Note 2)						
t _{d(on)}	Turn-On Delay Time	V _{DD} = 15 V, I _D = 1 A, V _{GS} = 10 V, R _{GEN} = 6 Ω		6	12	ns
t _r	Turn-On Rise Time			10	18	ns
t _{d(off)}	Turn-Off Delay Time			18	29	ns
t _f	Turn-Off Fall Time			5	12	ns
Q _g	Total Gate Charge	V _{DS} = 15V, I _D = 10 A, V _{GS} = 10 V		22	31	nC
Q _{gs}	Gate-Source Charge			3		nC
Q _{gd}	Gate-Drain Charge			4		nC

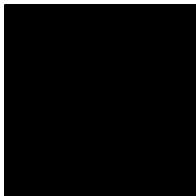
Electrical Characteristics

$T_A = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
Drain-Source Diode Characteristics and Maximum Ratings						
I_S	Maximum Continuous Drain-Source Diode Forward Current			3.2	A	
V_{SD}	Drain-Source Diode Forward Voltage	$V_{GS} = 0 \text{ V}$, $I_S = 3.2 \text{ A}$ (Note 2)		0.7	1.2	V

Notes:

1. R_{\thetaJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R_{\thetaJC} is guaranteed by design while R_{\thetaCA} is determined by the user's board design.



a) $R_{\thetaJA} = 45^\circ\text{C}/\text{W}$ when mounted on a 1 in² pad of 2 oz copper



b) $R_{\thetaJA} = 96^\circ\text{C}/\text{W}$ when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width < 300 μs , Duty Cycle < 2.0%

3. Maximum current is calculated as:

$$\sqrt{\frac{P_D}{R_{DS(ON)}}}$$

where P_D is maximum power dissipation at $T_C = 25^\circ\text{C}$ and $R_{DS(ON)}$ is at $T_{J(max)}$ and $V_{GS} = 10\text{V}$. Package current limitation is 21A

Typical Characteristics

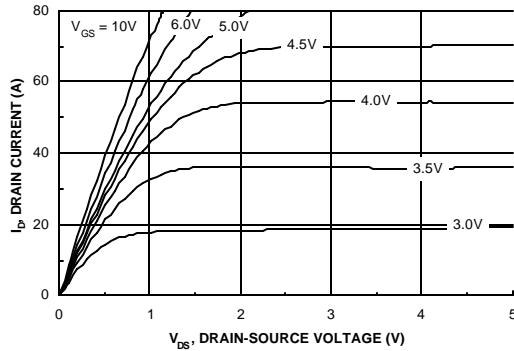


Figure 1. On-Region Characteristics

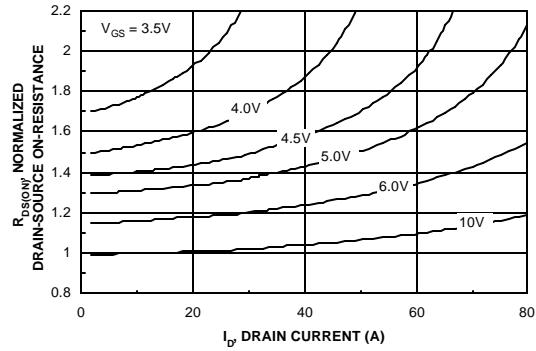


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage

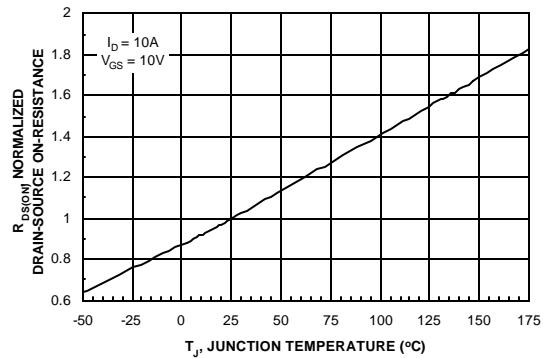


Figure 3. On-Resistance Variation with Temperature

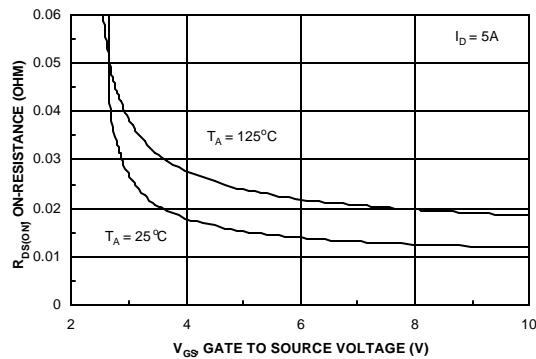


Figure 4. On-Resistance Variation with Gate-to-Source Voltage

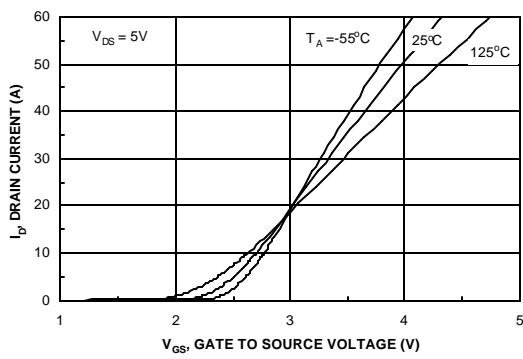


Figure 5. Transfer Characteristics

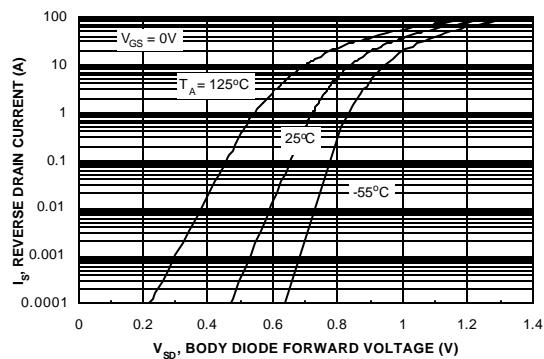


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature

Typical Characteristics

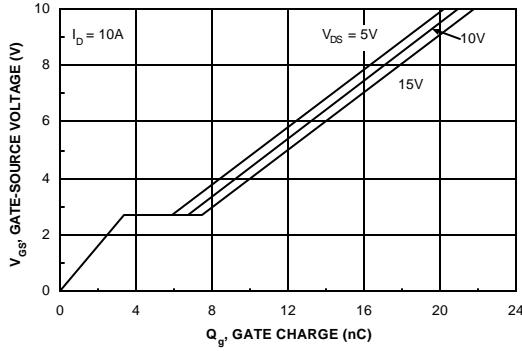


Figure 7. Gate Charge Characteristics

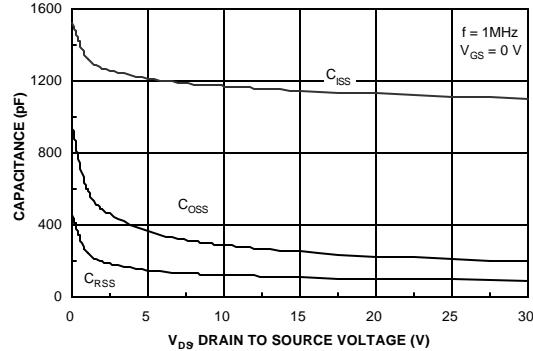


Figure 8. Capacitance Characteristics

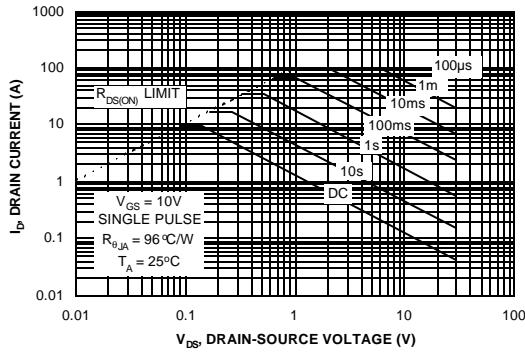


Figure 9. Maximum Safe Operating Area

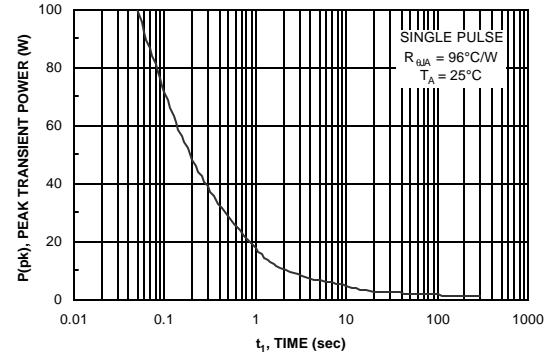


Figure 10. Single Pulse Maximum Power Dissipation

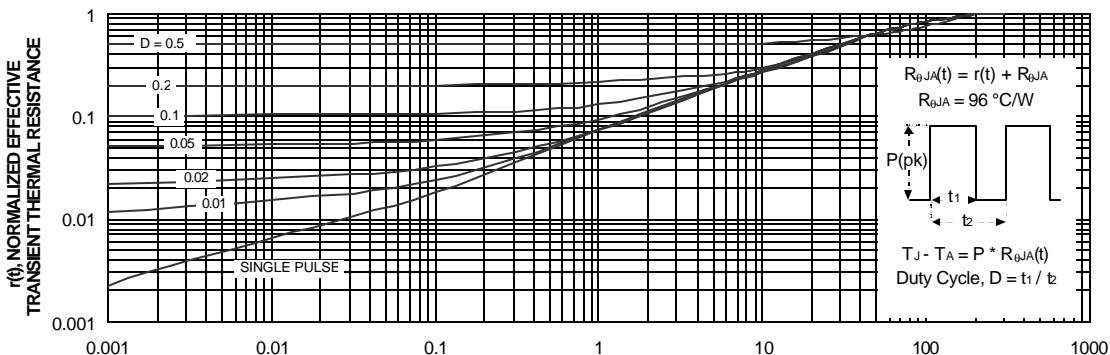


Figure 11. Transient Thermal Response Curve

Thermal characterization performed using the conditions described in Note 1b.
Transient thermal response will change depending on the circuit board design.

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